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07977-052001Application No.
08/690,747**Information Disclosure Statement
by Applicant**

(Use several sheets if necessary)

(37 CFR §1.98(b))

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Applicant
Hisashi Ohtani et alFiling Date
August 1, 1996Group Art Unit
1765

U.S. Patent Documents							
Examiner Initial	Desig. ID	Patent Number	Issue Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA	5,956,579	09/21/99	Yamazaki et al.			
	AB	6,072,193	06/06/00	Ohnuma et al.			RECEIVED
	AC	6,066,518	05/23/00	Yamazaki			MAR 01 2001
	AD	5,244,819	09/14/93	Yue			TC 1700
	AE	4,371,403	02/01/83	Ikubo et al.			
	AF						
	AG						
	AH						
	AI						
	AJ						
	AK						

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AL	5-109737	April 30, 1993	Japan			X	
	AM							
	AN							
	AO							
	AP							

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
	AQ	A. Ourmazd, "Gettering of Impurities in Silicon," Materials Research Society, Vol. 59, 1986, pp.331-340.
	AR	A. Ourmazd, et al., "Gettering of Metallic Impurities in Silicon," Materials Research Society, Vol. 36, 1985, pp. 25-30.
	AS	Etienne G. Colas, et al., "Quantitative Study of Metal Gettering in Silicon," Materials Research Society, Vol. 59, 1986, pp. 341-346.
	AT	K. Graff et al., "Palladium Test: A Tool to Evaluate Gettering Efficiency," Materials Research Society, Vol. 36, 1985, pp. 19-24.

Examiner Signature

Date Considered

3/17/01

EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.